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contents

Foreword

Keynote address abstract

PLATFORM TECHNICAL PRESENTATIONS

NBTI-1

The effect of recovery on NBTI characterization of thick non-nitrided oxides <i>H. Reisinger, R.P. Vollertsen, P.J. Wagner, S. Aresu, W. Gustin, T. Grasser, C. Schlünder</i>	1
Total recovery of defects generated by negative bias temperature instability <i>C. Benard, J.-L. Ogier, and D. Goguenheim</i>	7
Advanced On-The-Fly method with correction of initial values to characterize negative bias temperature instability reliability <i>C. Benard, J.-L. Ogier, and D. Goguenheim</i>	12

Back-end Reliability

Copper line topology impact on the reliability of SiOCH low-k dielectrics for the advanced 45 nm technology node and beyond <i>M. Vilmy, D. Roy, C. Monget, F. Volpi, J-M. Chaix</i>	16
Impact of oxygen vacancies profile and fringe effect on leakage current instability of tantalum pentoxide metal-insulator-metal (MIM) capacitors <i>Vi. Martinez, C. Besset, F. Monsieur, L. Montès, G. Ghibaudo</i>	21
The influence of complex geometries and stress non-uniformity on reliability <i>A. Aal</i>	25
Stress characterization for stress-induced voiding in Cu/Low K interconnects with geometry and upper cap layer dependences <i>M. Lin, J.W. Liang, and K.C. Su</i>	32

Reliability of Sensors/Memories

Ageing under illumination of MOS transistors for active pixel sensors (APS) applications <i>D. Lopez, F. Monsieur, S. Ricq, J.-M. Roux, and F. Balestra</i>	36
Investigation of GIDL current Injection disturb mechanism in two-transistor-eNVM memory devices <i>S.R. Kim, K.J. Han, J. Lee, P.Y. Lee, T. Zhou, K.-S. Lee, P. Liu, H.C. Tseng, B. Conguist</i>	40

High-k Reliability

Effect of substrate hot carrier stress on high-k gate stack <i>H. Park, G. Bersuker, C. Y. Kang, C. Young, H-H Tseng, R. Jammy</i>	44
Temperature (6-300K) dependence comparison of HfO ₂ /SiO ₂ and SiO ₂ MOS gate stacks <i>R.G. Southwick III, J. Reed, C. Buu, H. Bui, G. Bersuker, W.B. Knowlton</i>	48
Positive bias temperature instability effects in advanced high-k / metal gate NMOSFETs <i>D.P. Ioannou, S. Mittl, G. LaRosa</i>	55
Breakdown mechanism for the thin EOT Dy ₂ O ₃ /HfO ₂ dielectric <i>T. Lee, S. Park, J. Lee, S. K. Banerjee</i>	58

NBTI-2

Geometry effects on the NBTI degradation of PMOS transistors
G. Math, C. Benard, J.-L. Ogier, D. Goguenheim 60

Study of transistor and product NBTI lifetime distributions
J. Qin, B. Yan, Y. Shoshany, D. Roy, H. Rahamim, J.B. Bernstein 64

Reliability of Compound Materials and Devices

Interface traps in silicon carbide MOSFETs
C.J. Cochrane, P.M. Lenahan, A.J. Lelis 68

Effect of threshold-voltage instability on SIC DMOSFET reliability
A.J. Lelis, D. Habersat, R. Green, N. Goldsman 72

Coupled approach for reliability study of fully self aligned SiGe:C 250 GHz HBTs
M. Diop, N. Revil, M. Marin, F. Monsieur, T. Schwartzmann, G. Ghibaudo 77

fWLR Reliability

Quantitative reliability assessment of plasma induced damage on product wafers with fast WLR measurements
A. Martin, C. Bukethal, K.-H. Rydén, S. Baier, M. Schwerd 81

Negative bias temperature stress on PFETs within fast wafer level reliability monitoring
R.-P. Vollertsen, H. Reisinger, C. Schlünder 86

Late News

Defect creation stimulated by thermally activated hole trapping as the driving force behind negative bias temperature instability in SiO₂, SiON, and high-k gate stacks
T. Grasser, B. Kaczer, T. Aichinger, W. Gös, and M. Nelhiebel 91

The effect of the subthreshold slope degradation on NBTI device characterization
D. Brisbin and P. Chaparala 96

Reliability guardband reduction by differential targeting of pMOS gate oxide thickness
R. Geilenkeuser, K. Wieczorek, M. Trentzsch, F. Graetsch, B. Bayha, V. Samohvalov, T. Paetzold, and T. Schink 100

The origins of random telegraph noise in highly scaled SiON nMOSFETs
J.P. Campbell, J. Qin, K.P. Cheung, L. Yu, J.S. Suehle, A. Oates, and K. Sheng 105

POSTER PRESENTATIONS—REFEREED

Repeatability and stress level dependence on ESD-CDM testing for microelectronic components
Y. Satirakul, T. Butngam, and S. Phunyapinuant 110

Concept and implementation of an *in-situ* test structure for HTGS reliability testing of Power FETs on a wafer level basis
S. Baier 114

Fully automatical test and qualification system for a high endurance embedded EEPROM module
J. Fellner, G. Schatzberger, and A. Wiesner 118

A robust single event upset hardened clock distribution network
A.S. Mallajosyula and P. Zarkesh-Ha 121

Reliability simulation and design consideration of high speed ADC circuits
B. Yan, J. Qin, J. Dai, Q. Fan, and J.B. Bernstein 125

Dispersion and the worst case of thermal fatigue life of solder joints in vehicle electronic devices
T. Maruoka, Q. Yu, T. Shibusaki, and H. Miyauchi 129

A comparison between V-ramp TDDB techniques for reliability evaluation
A. Aal 133

An electrically-detected magnetic resonance study of the atomic-scale effects of fluorine on the negative bias temperature instability
J.T. Ryan, P.M. Lenahan, A.T. Krishnan, S. Krishnan, J.P. Campbell 137

Oxide reliability of SiC MOS devices <i>L. Yu, K.P. Cheung, J. Campbell, J.S. Suehle, and K. Sheng</i>	141
TUTORIAL ABSTRACTS	
Circuit Failure Prediction for Robust System Design in Scaled CMOS <i>Subhasish Mitra</i>	145
Measurement Issues for High-k Technology including NBTI <i>Chadwin Young</i>	145
JEDEC Overview <i>Alvin Strong</i>	145
Toward Understanding Negative Bias Temperature Instability <i>Tibor Grasser</i>	145
eFuse Design and Reliability <i>William Tonti</i>	145
Reliability of “Future” Devices <i>Wilfried Haensch</i>	145
DISCUSSION GROUP (DG) REPORTS	
DG: fast Wafer Level Reliability (fWLR) monitoring	146
DG: NVM reliability	150
DG: NBTI	151
DG: Dielectric electrical characterization	152
DG: Product reliability	153
BIOGRAPHIES	154
PICTURES	157